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Team Nexperia

# PMP4201V; PMP4201G; PMP4201Y

## NPN/NPN matched double transistors

Rev. 04 — 28 August 2009

**Product data sheet** 

## 1. Product profile

### 1.1 General description

NPN/NPN matched double transistors in small Surface-Mounted Device (SMD) plastic packages. The transistors in the SOT666 and SOT363 (SC-88) packages are fully isolated internally.

Table 1. Product overview

Type number	Package	age NPN/NPN h <sub>FE1</sub> /h <sub>FE2</sub>		PNP/PNP	
	NXP	JEITA	0.95 complement	complement	
PMP4201V	SOT666	-	PMP4501V	PMP5201V	
PMP4201G	SOT353	SC-88A	PMP4501G	PMP5201G	
PMP4201Y	SOT363	SC-88	PMP4501Y	PMP5201Y	

#### 1.2 Features

- Current gain matching
- Base-emitter voltage matching
- Common emitter configuration for SOT353 types
- Application-optimized pinout

#### 1.3 Applications

- Current mirror
- Differential amplifier

#### 1.4 Quick reference data

Table 2. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per transis	stor					
$V_{CEO}$	collector-emitter voltage	open base	-	-	45	V
I <sub>C</sub>	collector current		-	-	100	mA
h <sub>FE</sub>	DC current gain	$V_{CE} = 5 \text{ V};$ $I_{C} = 2 \text{ mA}$	200	290	450	



# PMP4201V; PMP4201G; PMP4201Y

**NPN/NPN** matched double transistors

Table 2. Quick reference data ...continued

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per device						
h <sub>FE1</sub> /h <sub>FE2</sub>	h <sub>FE</sub> matching	$V_{CE} = 5 V;$ $I_{C} = 2 \text{ mA}$	<u>[1]</u> 0.98	1	-	
$V_{BE1}-V_{BE2}$	V <sub>BE</sub> matching	$V_{CE} = 5 V;$ $I_{C} = 2 \text{ mA}$	[2] _	-	2	mV

<sup>[1]</sup> The smaller of the two values is taken as the numerator.

## 2. Pinning information

Table 3. Pinning

Table 3.	Pinning		
Pin	Description	Simplified outline	Symbol
SOT666;	; SOT363		
1	base TR1		2 5 4
2	base TR2	6 5 4	6 5 4
3	collector TR2		TR1 TR2
4	emitter TR2		
5	emitter TR1		1 2 3 006aaa548
6	collector TR1	001aab555	000aaa540
SOT353			
1	base TR1	Π- Π.	_
2	emitter TR1, TR2	5 4	5 4
3	base TR2		TR1 TR2
4	collector TR2		
5	collector TR1	<u> </u>	1 2 3 006aaa549

## 3. Ordering information

Table 4. Ordering information

PMP4201V - plastic surface-mounted package; 6 leads SOT666 PMP4201G SC-88A plastic surface-mounted package; 5 leads SOT353	Type number	Package	Package						
PMP4201G SC-88A plastic surface-mounted package; 5 leads SOT353		Name	Description	Version					
patient contact patients, contact	PMP4201V	-	plastic surface-mounted package; 6 leads	SOT666					
PMP4201Y SC-88 plastic surface-mounted package; 6 leads SOT363	PMP4201G	SC-88A	plastic surface-mounted package; 5 leads	SOT353					
	PMP4201Y	SC-88	plastic surface-mounted package; 6 leads	SOT363					

<sup>[2]</sup> The smaller of the two values is subtracted from the larger value.

## 4. Marking

Table 5. Marking codes

Type number	Marking code <sup>[1]</sup>
PMP4201V	EA
PMP4201G	R7*
PMP4201Y	S7*

<sup>[1] \* = -:</sup> made in Hong Kong

## 5. Limiting values

Table 6. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
Per transis	stor				
$V_{CBO}$	collector-base voltage	open emitter	-	50	V
$V_{CEO}$	collector-emitter voltage	open base	-	45	V
$V_{EBO}$	emitter-base voltage	open collector	-	6	V
Ic	collector current		-	100	mA
I <sub>CM</sub>	peak collector current	single pulse; $t_p \le 1 \text{ ms}$	-	200	mA
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C			
	SOT666		[1][2]	200	mW
	SOT353		[1] _	200	mW
	SOT363		[1] _	200	mW
Per device	•				
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C			
	SOT666		[1][2] _	300	mW
	SOT353		<u>[1]</u> _	300	mW
	SOT363		<u>[1]</u> _	300	mW
Tj	junction temperature		-	150	°C
T <sub>amb</sub>	ambient temperature		-65	+150	°C
T <sub>stg</sub>	storage temperature		-65	+150	°C

<sup>[1]</sup> Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

<sup>\* =</sup> p: made in Hong Kong

<sup>\* =</sup> t: made in Malaysia

<sup>\* =</sup> W: made in China

<sup>[2]</sup> Reflow soldering is the only recommended soldering method.

## 6. Thermal characteristics

Table 7. Thermal characteristics

Table 7.	Thermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per trans	istor					
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air				
	SOT666		[1][2]	-	625	K/W
	SOT353		[1] -	-	625	K/W
	SOT363		[1] -	-	625	K/W
Per device	e					
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air				
	SOT666		[1][2]	-	416	K/W
	SOT353		<u>[1]</u> -	-	416	K/W
	SOT363		<u>[1]</u> -	-	416	K/W

<sup>[1]</sup> Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

#### 7. Characteristics

Table 8. Characteristics

T<sub>amb</sub> = 25 °C unless otherwise specified

Symbol	Parameter	Conditions	Min	Тур	Max	Unit		
Per transistor								
I <sub>CBO</sub>	collector-base cut-off current	$V_{CB} = 30 \text{ V};$ $I_E = 0 \text{ A}$	-	-	15	nA		
		$V_{CB} = 30 \text{ V};$ $I_{E} = 0 \text{ A};$ $T_{j} = 150 ^{\circ}\text{C}$	-	-	5	μΑ		
I <sub>EBO</sub>	emitter-base cut-off current	$V_{EB} = 5 V;$ $I_C = 0 A$	-	-	100	nA		
h <sub>FE</sub>	DC current gain	$V_{CE} = 5 V;$ $I_{C} = 10 \mu A$	-	250	-			
		$V_{CE} = 5 V;$ $I_{C} = 2 \text{ mA}$	200	290	450			
V <sub>CEsat</sub>	collector-emitter saturation voltage	$I_{C} = 10 \text{ mA};$ $I_{B} = 0.5 \text{ mA}$	-	50	200	mV		
		$I_{C} = 100 \text{ mA};$ $I_{B} = 5 \text{ mA}$	-	200	400	mV		
V <sub>BEsat</sub>	base-emitter saturation voltage	$I_{C} = 10 \text{ mA};$ $I_{B} = 0.5 \text{ mA}$	[1] _	760	-	mV		
		$I_{C} = 100 \text{ mA};$ $I_{B} = 5 \text{ mA}$	[1] _	910	-	mV		

<sup>[2]</sup> Reflow soldering is the only recommended soldering method.

**Table 8.** Characteristics ...continued  $T_{amb} = 25 \,^{\circ}C$  unless otherwise specified

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
$V_{BE}$	base-emitter voltage	$V_{CE} = 5 \text{ V};$ $I_{C} = 2 \text{ mA}$	[2]	610	660	710	mV
		$V_{CE} = 5 V;$ $I_{C} = 10 \text{ mA}$	[2]	-	-	770	mV
C <sub>c</sub>	collector capacitance	$V_{CB} = 10 \text{ V};$ $I_E = i_e = 0 \text{ A};$ $f = 1 \text{ MHz}$		-	-	1.5	pF
C <sub>e</sub>	emitter capacitance	$V_{EB} = 0.5 \text{ V};$ $I_{C} = i_{c} = 0 \text{ A};$ $f = 1 \text{ MHz}$		-	11	-	pF
f <sub>T</sub>	transition frequency	$V_{CE} = 5 \text{ V};$ $I_{C} = 10 \text{ mA};$ $f = 100 \text{ MHz}$		100	250	-	MHz
NF	noise figure	$V_{CE} = 5 \text{ V};$ $I_{C} = 0.2 \text{ mA};$ $R_{S} = 2 \text{ k}\Omega;$ $f = 10 \text{ Hz to}$ $15.7 \text{ kHz}$		-	2.8	-	dB
		$V_{CE} = 5 \text{ V};$ $I_{C} = 0.2 \text{ mA};$ $R_{S} = 2 \text{ k}\Omega;$ $f = 1 \text{ kHz};$ $B = 200 \text{ Hz}$		-	3.3	-	dB
Per device							
h <sub>FE1</sub> /h <sub>FE2</sub>	h <sub>FE</sub> matching	$V_{CE} = 5 V;$ $I_{C} = 2 \text{ mA}$	[3]	0.98	1	-	
$V_{BE1}-V_{BE2}$	V <sub>BE</sub> matching	$V_{CE} = 5 V;$ $I_{C} = 2 \text{ mA}$	[4]	-	-	2	mV

<sup>[1]</sup>  $V_{BEsat}$  decreases by about 1.7 mV/K with increasing temperature.

<sup>[2]</sup> V<sub>BE</sub> decreases by about 2 mV/K with increasing temperature.

<sup>[3]</sup> The smaller of the two values is taken as the numerator.

<sup>[4]</sup> The smaller of the two values is subtracted from the larger value.

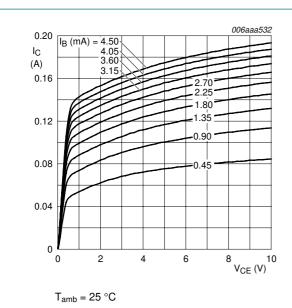
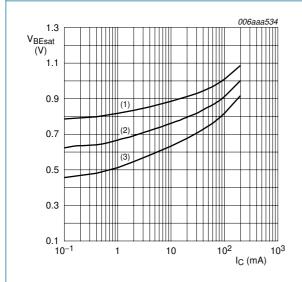


Fig 1. Collector current as a function of collector-emitter voltage; typical values



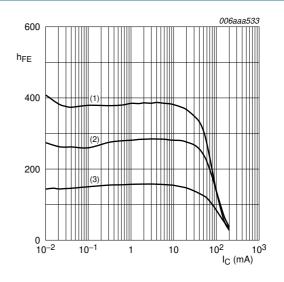
 $I_C/I_B = 20$ 

(1)  $T_{amb} = -55 \, ^{\circ}C$ 

(2)  $T_{amb} = 25 \, ^{\circ}C$ 

(3)  $T_{amb} = 100 \, ^{\circ}C$ 

Fig 3. Base-emitter saturation voltage as a function of collector current; typical values



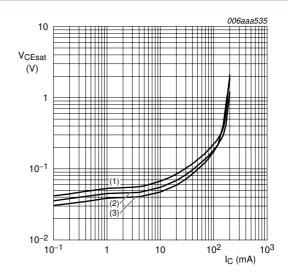
 $V_{CE} = 5 V$ 

(1)  $T_{amb} = 100 \, ^{\circ}C$ 

(2)  $T_{amb} = 25 \, ^{\circ}C$ 

(3)  $T_{amb} = -55 \, ^{\circ}C$ 

Fig 2. DC current gain as a function of collector current; typical values



 $I_{\rm C}/I_{\rm B} = 20$ 

(1)  $T_{amb} = 100 \, ^{\circ}C$ 

(2)  $T_{amb} = 25 \, ^{\circ}C$ 

(3)  $T_{amb} = -55 \, ^{\circ}C$ 

Fig 4. Collector-emitter saturation voltage as a function of collector current; typical values

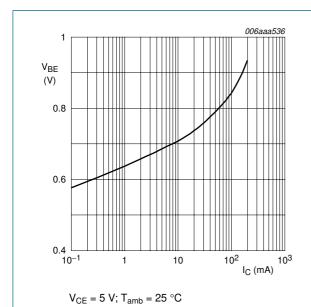


Fig 5. Base-emitter voltage as a function of collector current; typical values

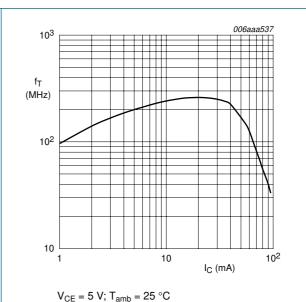


Fig 6. Transition frequency as a function of collector current; typical values

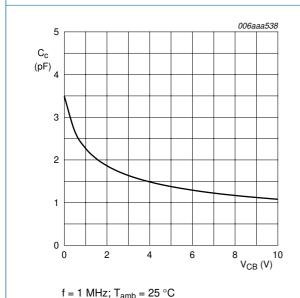


Fig 7. Collector capacitance as a function of collector-base voltage; typical values

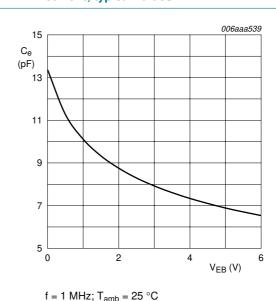
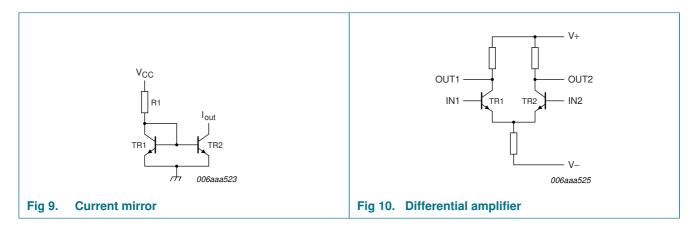
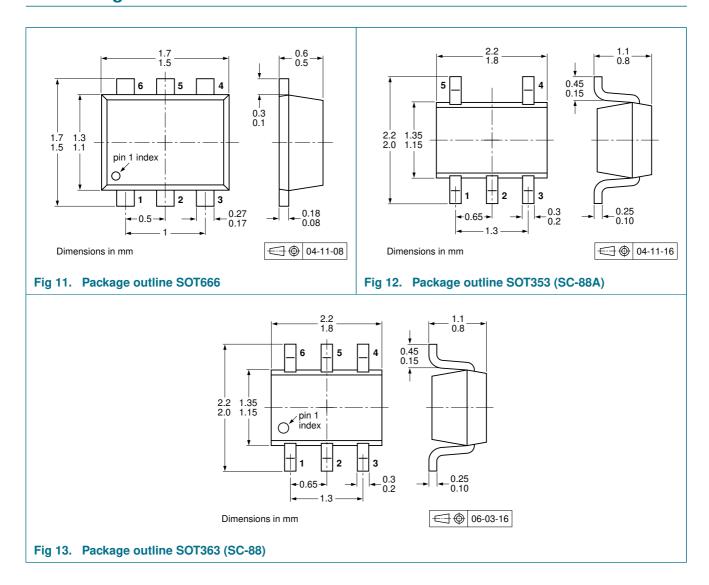


Fig 8. Emitter capacitance as a function of emitter-base voltage; typical values

# 8. Application information



## 9. Package outline



## 10. Packing information

Table 9. Packing methods

The indicated -xxx are the last three digits of the 12NC ordering code.[1]

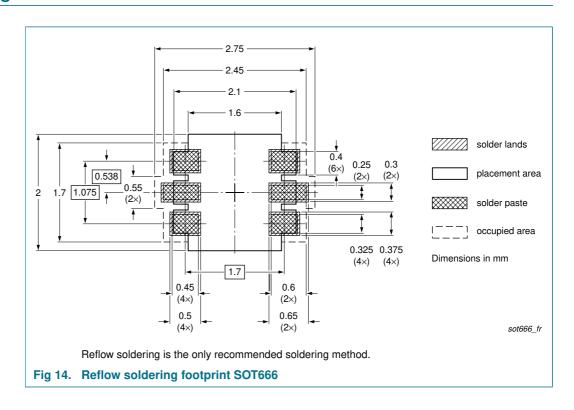
Туре	Package	Description		Packing quantity			
number	number			3000	4000	8000	10000
PMP4201V SOT666		2 mm pitch, 8 mm tape and reel		-	-	-315	-
		4 mm pitch, 8 mm tape and reel		-	-115	-	-
PMP4201G	SOT353	4 mm pitch, 8 mm tape and reel		-115	-	-	-135
PMP4201Y SOT36		4 mm pitch, 8 mm tape and reel; T1	[2]	-115	-	-	-135
		4 mm pitch, 8 mm tape and reel; T2	[3]	-125	-	-	-165

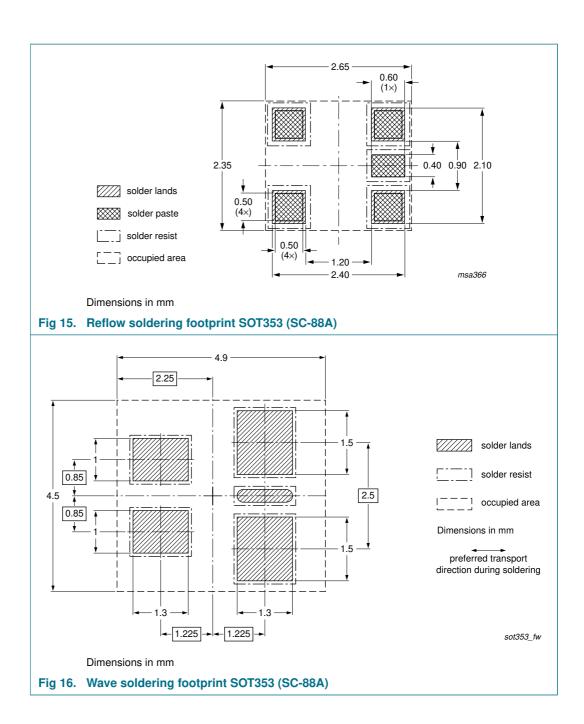
[1] For further information and the availability of packing methods, see Section 14.

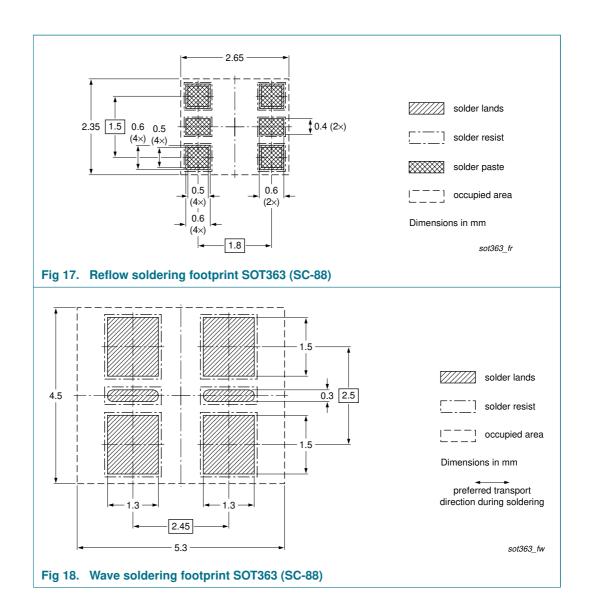
[2] T1: normal taping

[3] T2: reverse taping

## 11. Soldering







## 12. Revision history

## Table 10. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes			
PMP4201V_G_Y_4	20090828	Product data sheet	-	PMP4201V_G_Y_3			
Modifications:	<ul> <li>This data sheet was changed to reflect the new company name NXP Semiconductors, including new legal definitions and disclaimers. No changes were made to the technical content.</li> </ul>						
	<ul> <li>Figure 14 "</li> </ul>	Reflow soldering footprint S	SOT666": updated				
	<ul><li>Figure 16 "</li></ul>	Wave soldering footprint SC	OT353 (SC-88A)": update	ed			
	<ul> <li>Figure 17 "</li> </ul>	Reflow soldering footprint S	SOT363 (SC-88)": update	ed			
	<ul> <li>Figure 18 "</li> </ul>	Wave soldering footprint SC	OT363 (SC-88)": updated	t			
PMP4201V_G_Y_3	20060915	Product data sheet	-	PMP4201G_Y_2			
PMP4201G_Y_2	20060214	Product data sheet	-	PMP4201G_Y_1			
PMP4201G_Y_1	20060131	Product data sheet	-	-			

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Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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13 of 14

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# PMP4201V; PMP4201G; PMP4201Y

#### **NXP Semiconductors**

#### NPN/NPN matched double transistors

## 15. Contents

1	Product profile
1.1	General description
1.2	Features
1.3	Applications 1
1.4	Quick reference data 1
2	Pinning information 2
3	Ordering information 2
4	Marking 3
5	Limiting values 3
6	Thermal characteristics 4
7	Characteristics 4
8	Application information 8
9	Package outline 8
10	Packing information 9
11	Soldering 9
12	Revision history
13	Legal information
13.1	Data sheet status
13.2	Definitions
13.3	Disclaimers
13.4	Trademarks
14	Contact information
15	Contents 14

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